

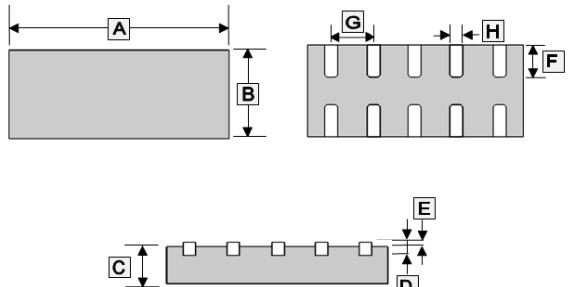
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

KS05UL5 is an ultra-low capacitance TVS designed to protect for high-speed data interfaces. With typical capacitance of 0.6pF only, KS05UL5 is designed to protest parasitic-sensitive systems against over-voltage and over-current transient events.

KS05UL5 uses ultra-small DFN2510 package. Each KS05UL5 device can protect four high-speed data lines. The combined features of ultra-low capacitance, ultra-small size and high ESD robustness make KS05UL5 ideal for high-speed data ports and high-frequency lines (e.g., HDMI &DVI) applications. The low clamping voltage of the KS05UL5 guarantees a minimum stress on the protected IC.

DFN2510

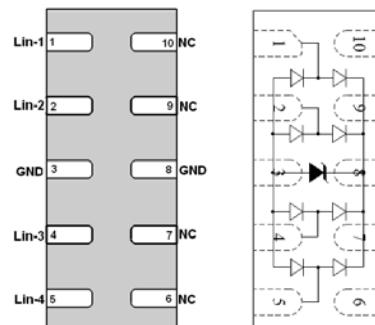


APPLICATIONS

- PCI Express
- Desktops, Servers and Notebooks
- MDDI Ports
- USB 2.0/3.0 Power and Data Line Protection
- Display Ports
- High Definition Multi-Media Interface(HDMI)
- Digital Visual Interface(DVI)

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.40	2.60	E	0.00	0.05
B	0.90	1.10	F	0.30	0.40
C	0.55TYP.		G	0.500 BSC.	
D	0.150 REF.		H	0.15	0.25

Pin Diagram



MARKING

0524P

PACKAGE INFORMATION

Package	MPQ	Leader Size
DFN2510	3K	7 inch

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
IEC 61000-4-2 (ESD)	V_{ESD}	± 25	kV
Contact discharge		± 17	
Peak pulse power ($tp=8/20\mu\text{s}$)	P_{PP}	30	W
Operating & Storage temperature range	T_J, T_{STG}	-55~125, -55~150	°C

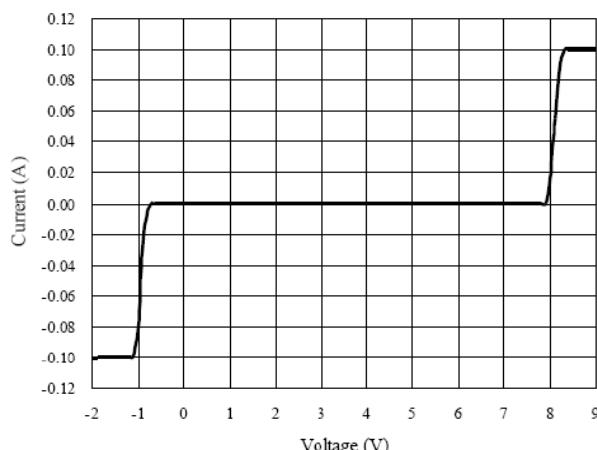
ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Reverse Working Voltage	V_{RWM}	Any I/O-to-GND	-	-	5	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$, Any I/O-to-GND	6	8	10	V
Reverse Leakage Current	I_R	$V_{RWM}=5\text{V}$, Any I/O-to-GND	-	0.1	1	μA
Clamping Voltage	V_C	$I_{PP}=1\text{A}$, $tp=8/20\mu\text{s}$, Any I/O-to-GND	-	-	12	V
Parasitic capacitance	C_{ESD}	I/O-to-GND, $V_R=0$, $f=1\text{MHz}$	-	0.6	0.8	pF
		I/O-to-I/O, $V_R=0$, $f=1\text{MHz}$	-	0.2	0.4	pF

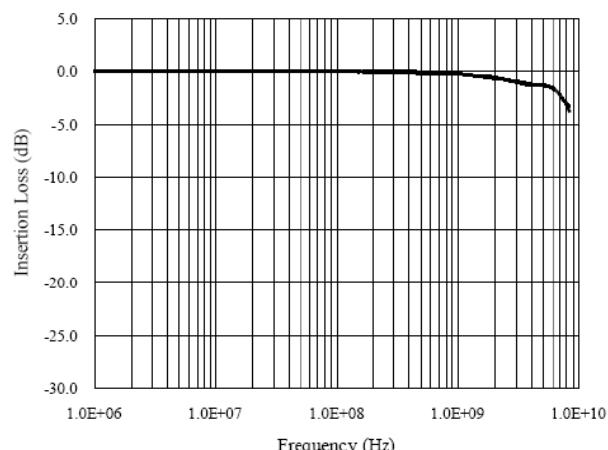
Note: I/O pins are pin 1,2,4,5.

RATINGS AND CHARACTERISTICS CURVES

Voltage Sweeping of I/O to GND

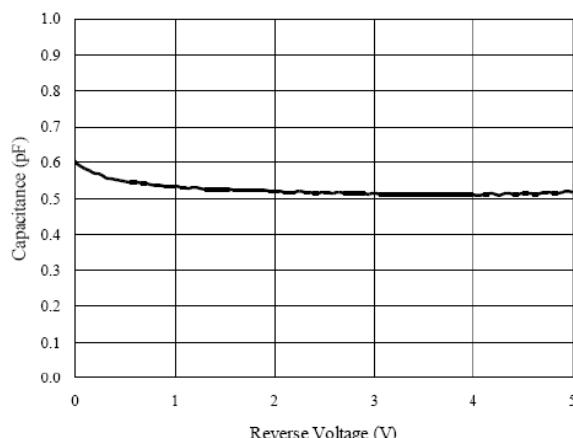


Insertion Loss S21 of I/O to GND

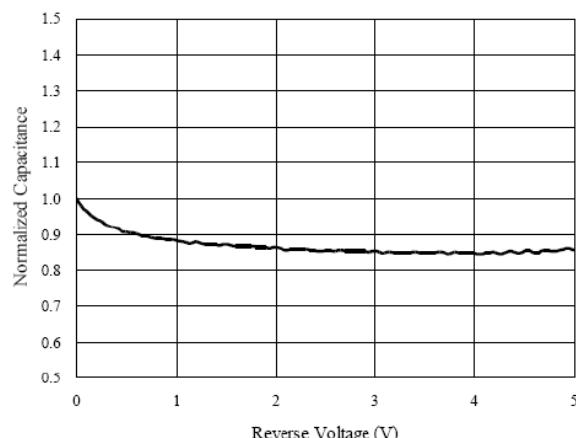


Capacitance vs. Voltage of I/O to GND ($f = 1\text{MHz}$)

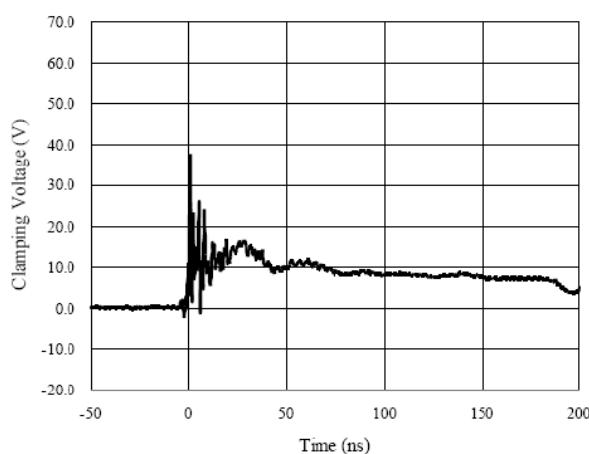
Capacitance vs. Reverse Voltage



Normalized Capacitance vs. Reverse Voltage



ESD Clamping of I/O to GND (+8kV Contact per IEC 61000-4-2)



ESD Clamping of I/O to GND (-8kV Contact per IEC 61000-4-2)

